100V 2.8mΩ N-Ch Power MOSFET

Features

- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- 100% UIS Tested, 100% R_g Tested

Product Summary

Parameter	Typ.	Unit
V_{DS}	100	V
$V_{GS(th)}$	1.6	V
I_D (@ V_{GS} = 10V) (1)	135	A
$R_{DS(ON)}$ (@ V_{GS} = 10V)	2.8	mΩ
$R_{DS(ON)}$ (@ V_{GS} = 4.5V)	3.4	mΩ

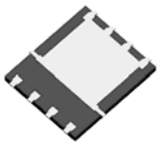
Applications

- Power Managerment in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems
- Motor Driving in Power Tool, E-vehicle, Robotics

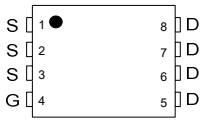
PDFN5x6

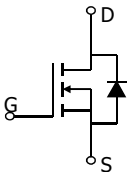
Top View

Bottom View



Top View
Pin Configuration





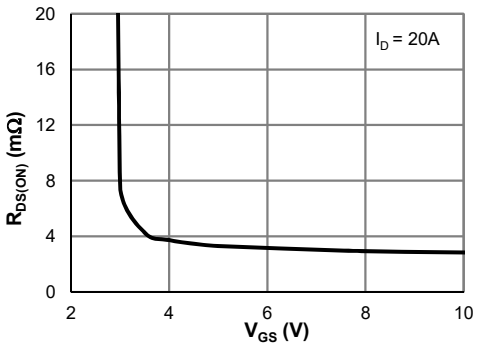
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSL1003AG-13	PDFN5x6	8	SL1003A	1	-55 to 150	13-inch Reel	3000

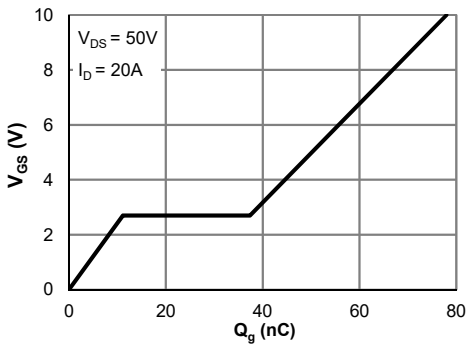
Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	100	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (1)	T_C = 25°C	I_D	135	A
	T_C = 100°C		85	
Continuous Drain Current (6)	T_C = 25°C	I_D	100	A
Pulsed Drain Current (2)		I_{DM}	483	A
Avalanche Current (3)		I_{AS}	72	A
Avalanche Energy (3)		E_{AS}	259	mJ
Power Dissipation (4)	T_C = 25°C	P_D	114	W
	T_C = 100°C		45	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

$R_{DS(ON)}$ vs. V_{GS}



Gate Charge



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Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1.0	μA
		T_J = 55°C			5.0	
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.2	1.6	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		2.8	3.4	mΩ
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 15A		3.4	4.3	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 20A		109		S
Diode Forward Voltage	V_{SD}	I_S = 1A, V_{GS} = 0V		0.7	1.0	V
Diode Continuous Current	I_S	T_C = 25°C			114	A
DYNAMIC PARAMETERS (5)						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		4646		pF
Output Capacitance	C_{oss}			1214		pF
Reverse Transfer Capacitance	C_{rss}			5.8		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS}= 0V, f = 1MHz		2.3		Ω
SWITCHING PARAMETERS (5)						
Total Gate Charge (@V_{GS} = 10V)	Q_g	V_{GS} = 0 to 10V V_{DS} = 50V, I_D = 20A		78		nC
Total Gate Charge (@V_{GS} = 6.0V)	Q_g			56		nC
Gate Source Charge	Q_{gs}			11.2		nC
Gate Drain Charge	Q_{gd}			26		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS} = 10V, V_{DS} = 50V R_L = 2.5Ω, R_{GEN} = 6Ω		10.0		ns
Turn-On Rise Time	t_r			22		ns
Turn-Off DelayTime	$t_{D(off)}$			84		ns
Turn-Off Fall Time	t_f			61		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A/μs		84		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 20A, dI_F/dt = 100A/μs		216		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	48	58	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.80	1.1	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} = 150°C.
3. This single-pulse measurement was taken under the following condition [L = 0.1mH, V_{GS} = 10V, V_{DS} = 50V] while its value is limited by T_{J_Max} = 150°C.
4. The power dissipation P_D is based on T_{J_Max} = 150°C.
5. This value is guaranteed by design hence it is not included in the production test.
6. Continuous current rating is limited by the package used.

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Typical Electrical & Thermal Characteristics

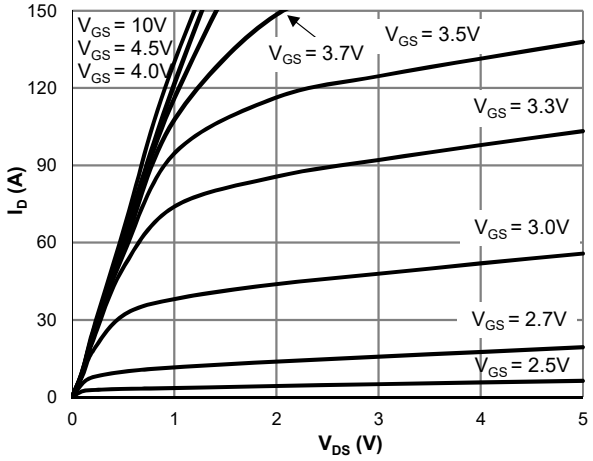

Figure 1: Saturation Characteristics

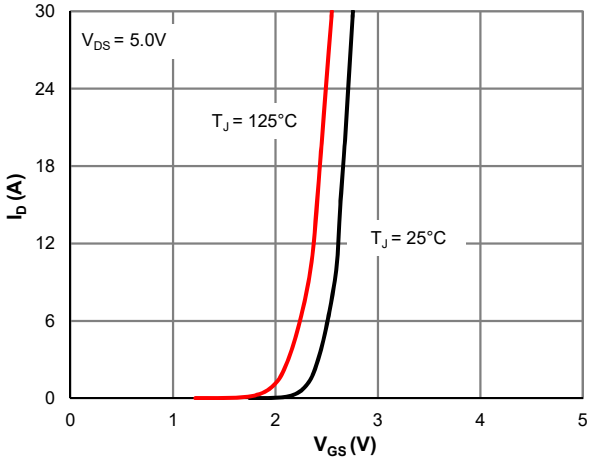

Figure 2: Transfer Characteristics

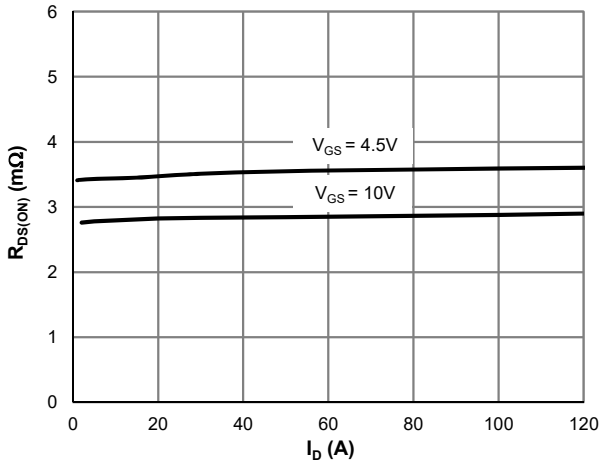

Figure 3: $R_{DS(ON)}$ vs. Drain Current

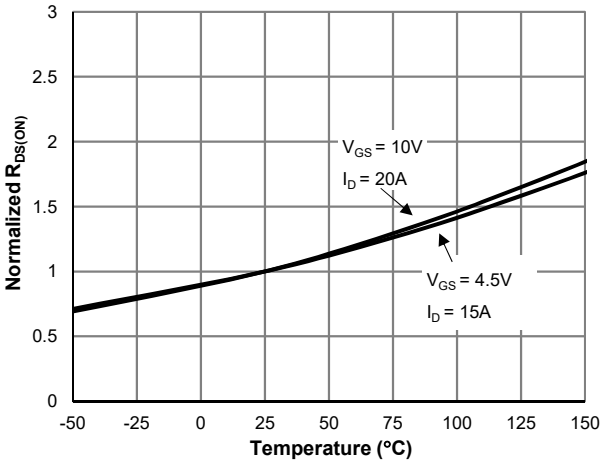

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

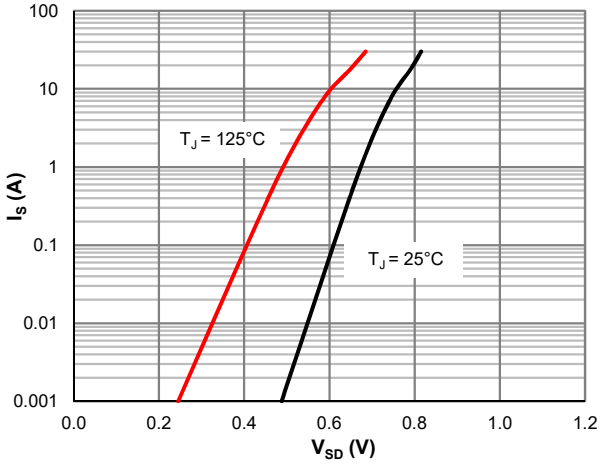

Figure 5: Body-Diode Characteristics

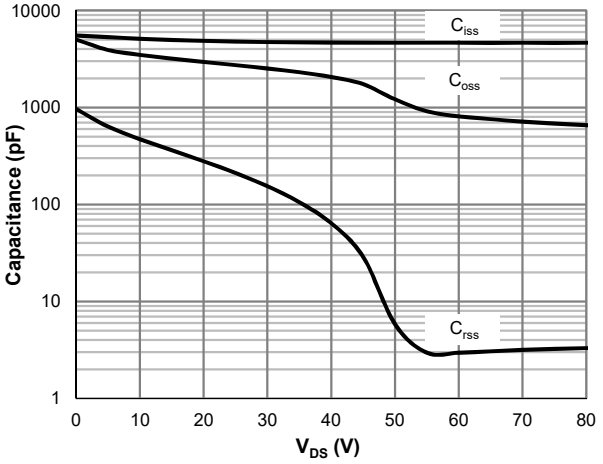

Figure 6: Capacitance Characteristics

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Typical Electrical & Thermal Characteristics

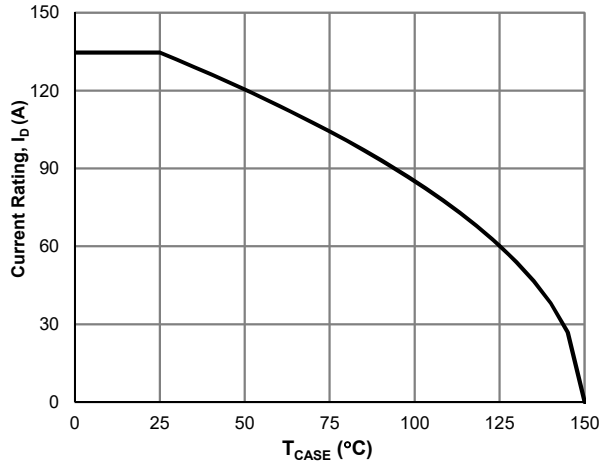

Figure 7: Current De-rating

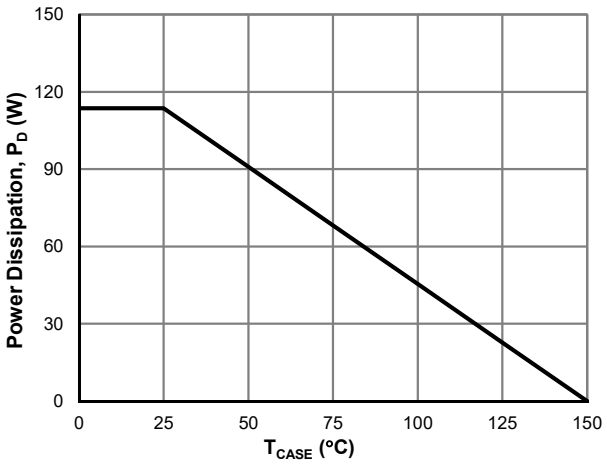

Figure 8: Power De-rating

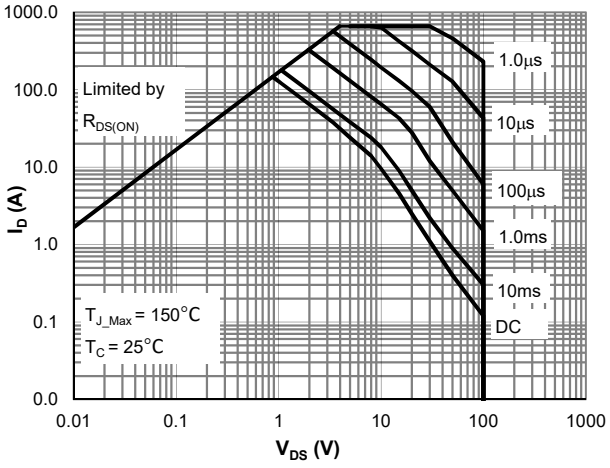

Figure 9: Maximum Safe Operating

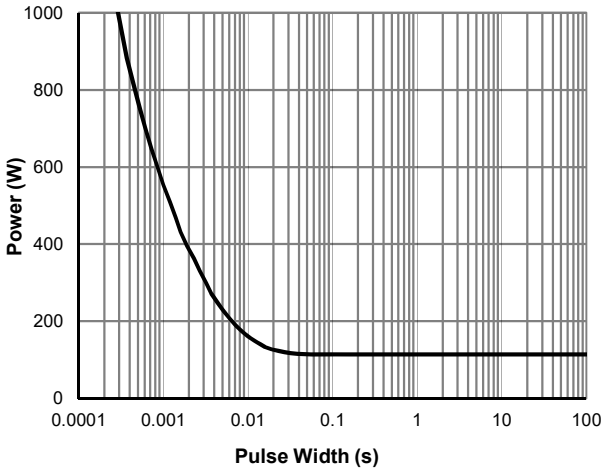

Figure 10: Single Pulse Power Rating, Junction-to-Case

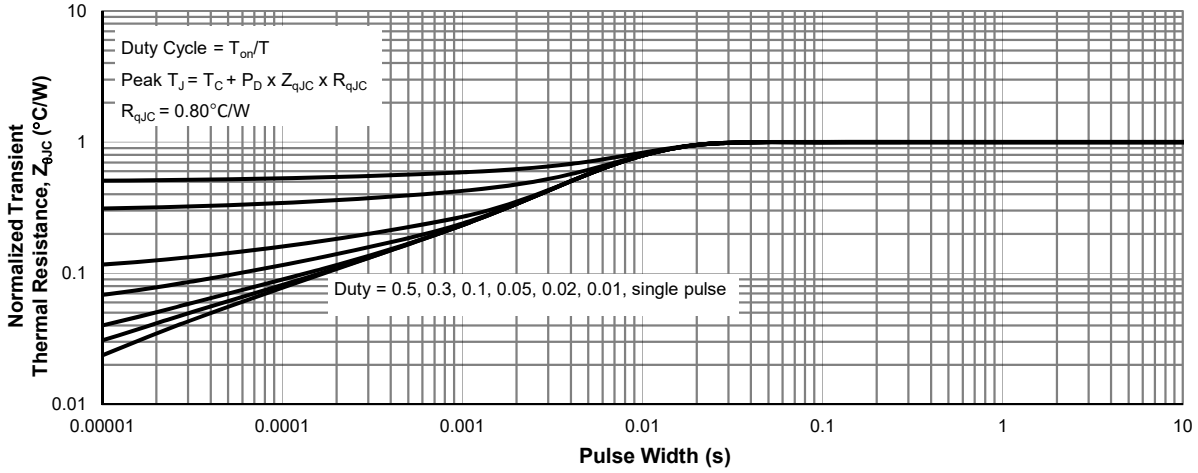

Figure 11: Normalized Maximum Transient Thermal Impedance

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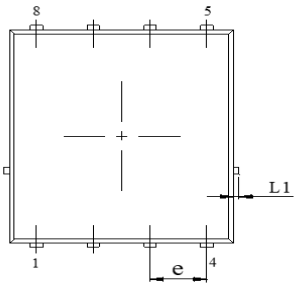
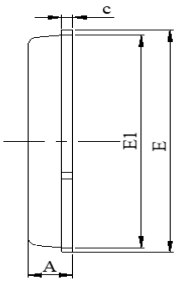
PDFN5x6 Package Information

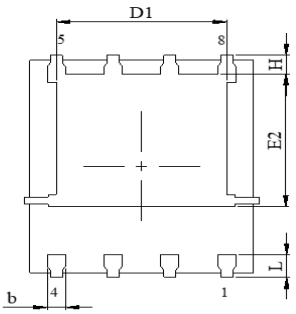
Package Outline



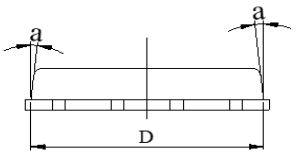
Top View



Side View



Bottom View

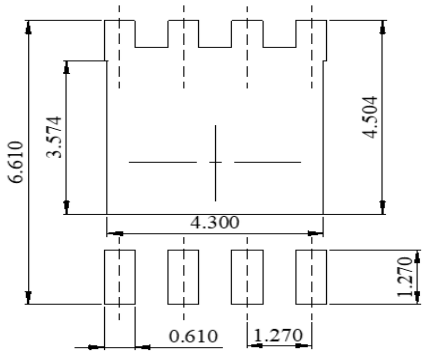


Front View

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETER	
	MIN.	MAX.
A	0.90	1.20
b	0.33	0.51
c	0.23	0.33
D	4.80	5.40
D1	3.61	4.25
E	5.90	6.30
E1	5.55	5.95
E2	3.35	3.95
e	1.27BSC	
H	0.41	0.80
L	0.51	0.80
L1	-	0.15
a	0°	12°

Recommended Footprint



DIMENSIONS:MILLIMETERS

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